S70GL-P MirrorBit® Flash

S70GL02GP
2 Gigabit, 3.0 Volt-only Page Mode Flash Memory featuring 90 nm MirrorBit Process Technology

Data Sheet

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General Description

The Spansion S70GL02GP 2-Gigabit Mirrorbit Flash memory device is fabricated on 90 nm process technology. This device offers a fast page access time of 25 ns with a corresponding random access time of 110 ns. It features a Write Buffer that allows a maximum of 32 words/64 bytes to be programmed in one operation, resulting in faster effective programming time than standard single byte/word programming algorithms. This makes the device an ideal product for today's embedded applications that require higher density, better performance and lower power consumption.

Distinctive Characteristics

- **Two 1024 Megabit (S29GL01GP) in a single 64-ball Fortified-BGA package (see publication S29GL-P_00 for full specifications)**
- **Single 3V read/program/erase (3.0V - 3.6V)**
- **90 nm MirrorBit process technology**
- **8-word/16-byte page read buffer**
- **32-word/64-byte write buffer reduces overall programming time for multiple-word writes**
- **Secured Silicon Sector region**
  - 128-word/256-byte sector for permanent, secure identification through an 8-word/16-byte random Electronic Serial Number
  - Can be programmed and locked at the factory or by the customer
- **Uniform 64Kword/128KByte Sector Architecture**
  - S70GL02GP: two thousand forty-eight sectors
- **100,000 erase cycles per sector typical**
- **20-year data retention typical**
- **Offered Packages**
  - 64-ball Fortified BGA

- **Suspend and Resume commands for Program and Erase operations**
- **Write operation status bits indicate program and erase operation completion**
- **Unlock Bypass Program command to reduce programming time**
- **Support for CFI (Common Flash Interface)**
- **Persistent and Password methods of Advanced Sector Protection**
- **WP#/ACC input**
  - Accelerates programming time (when V_{ACC} is applied) for greater throughput during system production
  - Protects first or last sector of each die, regardless of sector protection settings
- **Hardware reset input (RESET#) resets device**
- **Ready/Busy# output (RY/BY#) detects program or erase cycle completion**

Performance Characteristics

Max. Read Access Times (ns) (Note 1)	
Parameter	**2 Gb**
Random Access Time (t_{ACC})	110
Page Access Time (t_{PACC})	25
CE# Access Time (t_{CE})	110
OE# Access Time (t_{OE})	25

Notes

1. *Access times are dependent on V_{CC} and V_{IO} operating ranges. See Ordering Information on page 6 for further details.*

2. *Contact a sales representative for availability.*

Current Consumption (typical values)	
Random Access Read	30 mA
8-Word Page Read	1 mA
Program/Erase	50 mA
Standby	2 µA

Program & Erase Times (typical values)	
Single Word Programming	60 µs
Effective Write Buffer Programming (V_{CC}) Per Word	15 µs
Effective Write Buffer Programming (V_{ACC}) Per Word	15 µs
Sector Erase Time (64 Kword Sector)	0.5 s

Table of Contents

1. Ordering Information

The ordering part number is formed by a valid combination of the following:

```
S70GL02GP    11    F    F    C    R1    0
```

PACKING TYPE
0 = Tray (standard; see (Note 3)
2 = 7" Tape and Reel
3 = 13" Tape and Reel

MODEL NUMBER (V_{IO} range, protection when WP# =V_{IL})
R1 = V_{IO} = V_{CC} = 3.0 to 3.6V, highest address sector protected
R2 = V_{IO} = V_{CC} = 3.0 to 3.6V, lowest address sector protected

TEMPERATURE RANGE
I   = Industrial (–40°C to +85°C)
C = Commercial (0°C to +85°C)

PACKAGE MATERIALS SET
A = Pb (Note 1)
F = Pb-free

PACKAGE TYPE
F = Fortified Ball Grid Array, 1.0 mm pitch package

SPEED OPTION
11 = 110 ns

DEVICE NUMBER/DESCRIPTION
S70GL02GP
3.0 Volt-only, 2048 Megabit (128 M x 16-Bit/256 M x 8-Bit) Page-Mode Flash Memory
Manufactured on 90 nm MirrorBit process technology

1.1 Recommended Combinations

Recommended Combinations table below list various configurations planned to be available in volume. The table below will be updated as new combinations are released. Check with your local sales representative to confirm availability of specific configuration not listed or to check on newly released combinations.

S29GL-P Recommended Combinations (Note 1)					
Base OPN	**Speed (ns)**	**Package & Temperature**	**Model Number**	**Packing Type**	**Ordering Part Number (x = Packing Type)**
S70GL02GP	110	FFC, FAC (Note 2)	R1, R2	0, 2, 3 (Note 3)	S70GL02GP11FFCR1x S70GL02GP11FFCR2x S70GL02GP11FACR1x S70GL02GP11FACR2x

Notes
1. *Contact a local sales representative for availability.*
2. *BGA package marking omits leading "S29" and packing type designator from ordering part number.*
3. *Packing Type "0" is standard option.*

2. Input/Output Descriptions & Logic Symbol

Table 2.1 identifies the input and output package connections provided on the device.

Table 2.1 Input/Output Descriptions

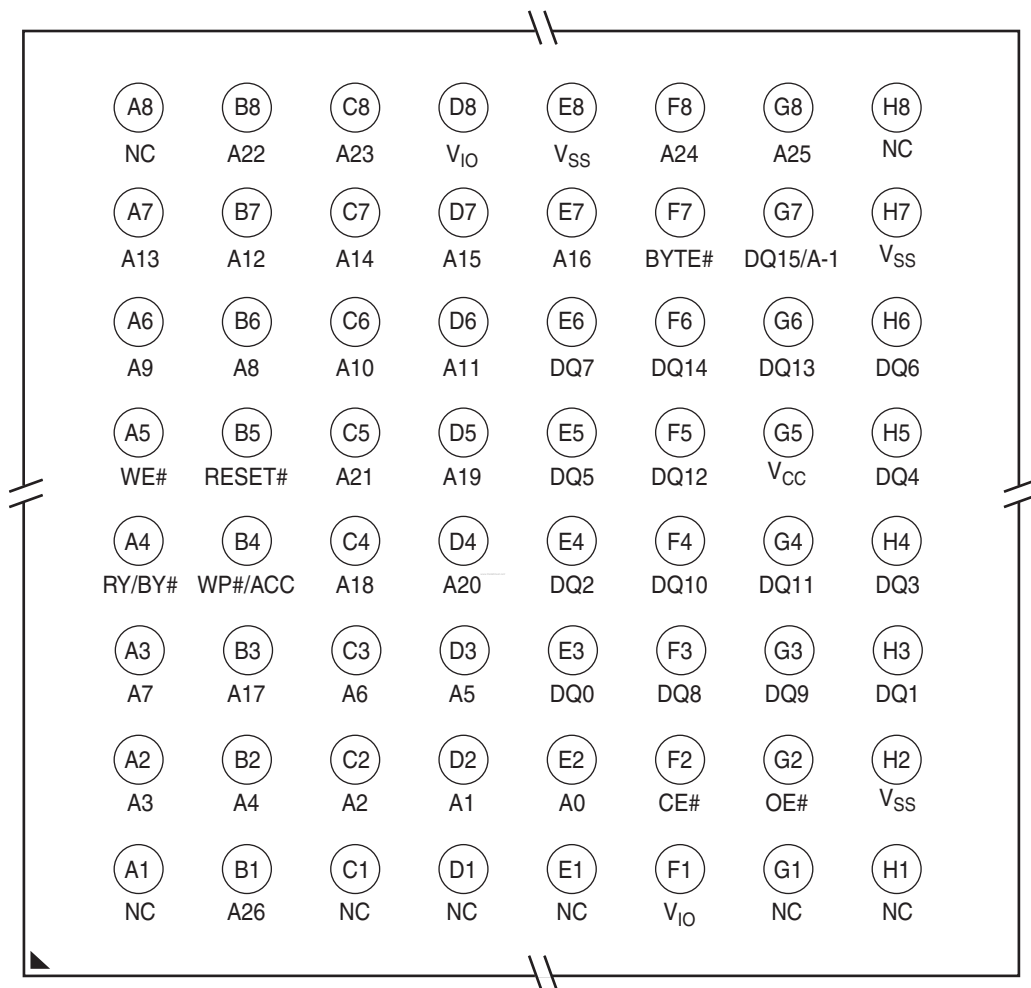| Symbol	Type	Description
A26–A0	Input	Address lines for GL02GP
DQ14–DQ0	I/O	Data input/output.
DQ15/A-1	I/O	DQ15: Data input/output in word mode. A-1: LSB address input in byte mode.
CE#	Input	Chip Enable.
OE#	Input	Output Enable.
WE#	Input	Write Enable.
V_{CC}	Supply	Device Power Supply.
V_{IO}	Supply	Versatile IO Input.
V_{SS}	Supply	Ground.
RY/BY#	Output	Ready/Busy. Indicates whether an Embedded Algorithm is in progress or complete. At V_{IL}, the device is actively erasing or programming. At High Z, the device is in ready.
BYTE#	Input	Selects data bus width. At V_{IL}, the device is in byte configuration and data I/O pins DQ0-DQ7 are active. At V_{IH}, the device is in word configuration and data I/O pins DQ0-DQ15 are active.
RESET#	Input	Hardware Reset. Low = device resets and returns to reading array data.
WP#/ACC	Input	Write Protect/Acceleration Input. At V_{IL}, disables program and erase functions in the outermost sectors. At V_{HH}, accelerates programming; automatically places device in unlock bypass mode. Should be at V_{IH} for all other conditions.
NC	No Connect	Not connected internally.

2.1   Special Handling Instructions for BGA Package

Special handling is required for Flash Memory products in BGA packages.

Flash memory devices in BGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

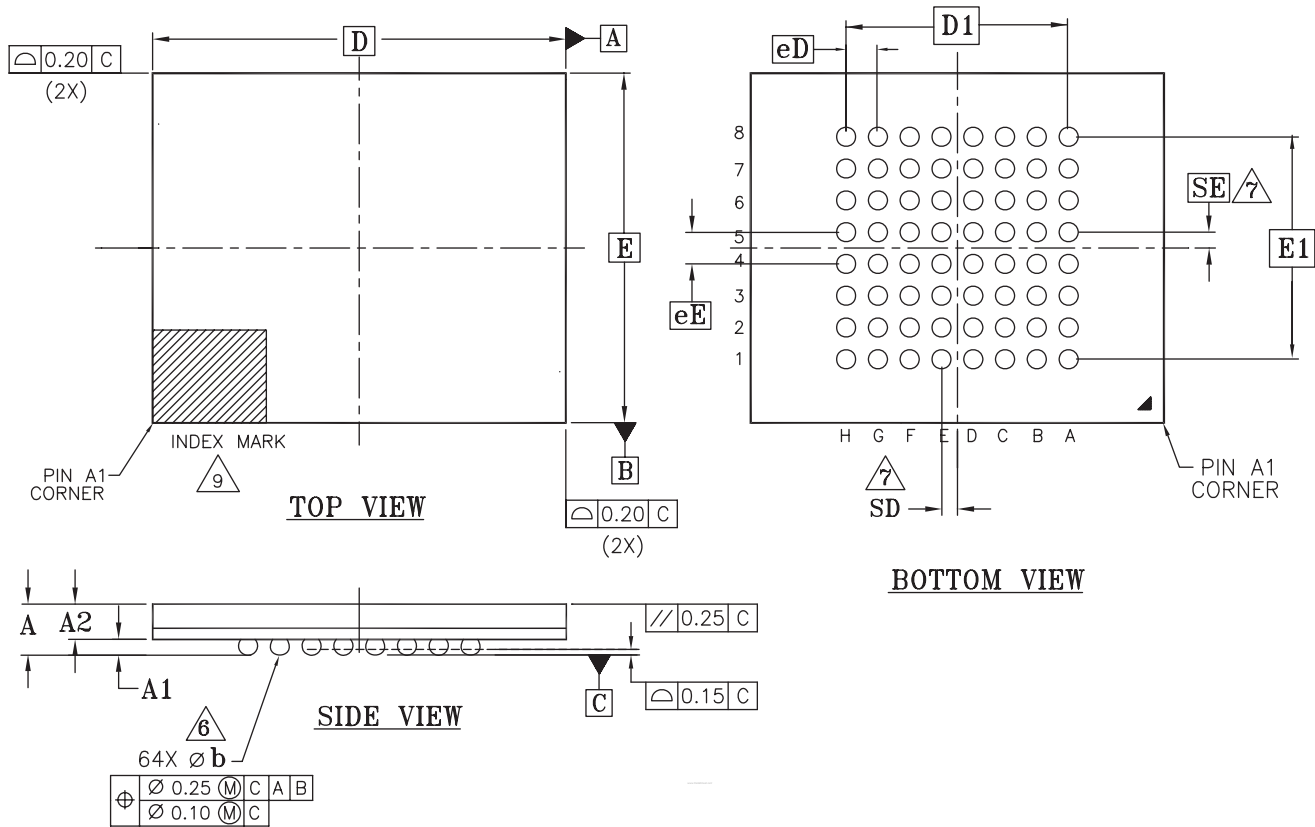**Figure 2.1** 64-ball Fortified Ball Grid Array

64-ball Fortified BGA
Top View, Balls Facing Down

A8	B8	C8	D8	E8	F8	G8	H8
NC	A22	A23	V_{IO}	V_{SS}	A24	A25	NC
A7	B7	C7	D7	E7	F7	G7	H7
A13	A12	A14	A15	A16	BYTE#	DQ15/A-1	V_{SS}
A6	B6	C6	D6	E6	F6	G6	H6
A9	A8	A10	A11	DQ7	DQ14	DQ13	DQ6
A5	B5	C5	D5	E5	F5	G5	H5
WE#	RESET#	A21	A19	DQ5	DQ12	V_{CC}	DQ4
A4	B4	C4	D4	E4	F4	G4	H4
RY/BY#	WP#/ACC	A18	A20	DQ2	DQ10	DQ11	DQ3
A3	B3	C3	D3	E3	F3	G3	H3
A7	A17	A6	A5	DQ0	DQ8	DQ9	DQ1
A2	B2	C2	D2	E2	F2	G2	H2
A3	A4	A2	A1	A0	CE#	OE#	V_{SS}
A1	B1	C1	D1	E1	F1	G1	H1
NC	A26	NC	NC	NC	V_{IO}	NC	NC

2.2   LSE064—64 ball Fortified Ball Grid Array, 13 x 11 mm

Figure 2.2 LSE064—64-ball Fortified Ball Grid Array (FBGA), 13 x 11 mm

NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.

2. ALL DIMENSIONS ARE IN MILLIMETERS.

3. BALL POSITION DESIGNATION PER JEP95, SECTION 4.3, SPP-010.

4. e REPRESENTS THE SOLDER BALL GRID PITCH.

5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

   n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.

6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.

7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2

8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

9. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

3611 \ 16-038.15 \ 11.13.6

PACKAGE	LSE 064			
JEDEC	N/A			
D x E	13.00 mm x 11.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
A	---	---	1.40	PROFILE
A1	0.40	---	---	BALL HEIGHT
A2	0.79	---	0.91	BODY THICKNESS
D	13.00 BSC.			BODY SIZE
E	11.00 BSC.			BODY SIZE
D1	7.00 BSC.			MATRIX FOOTPRINT
E1	7.00 BSC.			MATRIX FOOTPRINT
MD	8			MATRIX SIZE D DIRECTION
ME	8			MATRIX SIZE E DIRECTION
n	64			BALL COUNT
Øb	0.50	0.60	0.70	BALL DIAMETER
eE	1.00 BSC.			BALL PITCH
eD	1.00 BSC			BALL PITCH
SD / SE	0.50 BSC.			SOLDER BALL PLACEMENT
	---			DEPOPULATED SOLDER BALLS

3. Memory Map

The S70GL02GP consist of uniform 64 Kword (128 Kb) sectors organized as shown in Table 3.1.

Table 3.1 S70GL02GP Sector & Memory Address Map

Uniform Sector Size	Sector Count	Sector Range	Address Range (16-bit)	Notes
64 Kword/128 Kb	2048	SA00	0000000h–000FFFFh	Sector Starting Address
		:	:	
		SA2047	7FF0000H–7FFFFFFh	Sector Ending Address

Note

This table has been condensed to show sector-related information for an entire device on a single page. Sectors and their address ranges that are not explicitly listed (such as SA001-SA2046) have sector starting and ending addresses that form the same pattern as all other sectors of that size. For example, all 128 Kb sectors have the pattern xxx0000h-xxxFFFFh.

4. Autoselect

Table 4.1 provides the device identification codes for the S70GL02GP. For more information on the autoselect function, refer to the S29GL-P data sheet (publication number S29GL-P_00).

Table 4.1 Autoselect Addresses in System

Description	Address	Read Data (word/byte mode)
Manufacturer ID	(Base) + 00h	xx01h/1h
Device ID, Word 1	(Base) + 01h	227Eh/7Eh
Device ID, Word 2	(Base) + 0Eh	2248h/48h
Device ID, Word 3	(Base) + 0Fh	2201h/01h
Secure Device Verify	(Base) + 03h	For S70GL02GPH: XX19h/19h = Not Factory Locked. XX99h/99h = Factory Locked. For S70GL02GPL: XX09h/09h = Not Factory Locked. XX89h/89h = Factory Locked.
Sector Protect Verify	(SA) + 02h	xx01h/01h = Locked, xx00h/00h = Unlocked

5. Erase And Programming Performance

Table 5.1 Erase And Programming Performance

Parameter		Typ (Note 1)	Max (Note 2)	Unit	Comments
Sector Erase Time		0.5	3.5	sec	Excludes 00h programming prior to erasure (Note 3)
Chip Erase Time	S70GL02GP	1024	4096	sec	
Total Write Buffer Time, for 64 bytes		480		µs	Excludes system level overhead (Note 4)
Total Accelerated Write Buffer Programming Time, for 64 bytes		432		µs	
Chip Program Time	S70GL02GP	1968		sec	

Notes

1. *Typical program and erase times assume the following conditions: 25°C, 3.6 V V_{CC}, 10,000 cycles, checkerboard pattern.*

2. *Under worst case conditions of -40°C, V_{CC} = 3.0 V, 100,000 cycles.*

3. *In the pre-programming step of the Embedded Erase algorithm, all bits are programmed to 00h before erasure.*

4. *System-level overhead is the time required to execute the two- or four-bus-cycle sequence for the program command.*

6. BGA Package Capacitance

Parameter Symbol	Parameter Description	Test Setup	Typ	Max	Unit
C_{IN}	Input Capacitance	$V_{IN} = 0$	12	20	pF
C_{OUT}	Output Capacitance	$V_{OUT} = 0$	20	24	pF
C_{IN2}	Control Pin Capacitance	$V_{IN} = 0$	16	20	pF
RESET#, WP#/ACC	Separated Control Pin	$V_{IN} = 0$	84	90	pF
CE#	Separated Control Pin	$V_{IN} = 0$	44	50	pF

Notes
1. *Sampled, not 100% tested.*

2. *Test conditions $T_A = 25°C$, f = 1.0 MHz.*

7.   Revision History

Section	Description
Revision 01 (December 4, 2006)	
	Initial Release.
Revision 02 (May 19, 2008)	
Global	Changed data sheet designation Added Product Life-cycle notice Removed Table of Figures and Table of Tables
Ordering Information	- Changed sample OPN - Added Commercial temperature range - Changed configuration in "Device Number/description" - Modified "Recommended Combination" table & removed TSOP package option
Erase And Program Performance	Chip Program Time: removed comment
Common Flash Memory Interface	Removed section (see publication S29GL-P_00 for details)
Revision 03 (February 23, 2010)	
Global	Updated available model options. Corrected Chip Program Time.